

	Hits	Search Text	DBs
1	2	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) same (thin\$4 or etch\$4) same (secondary near5 electron) same (ioni\$4 near9 radiation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	20	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) same (thin\$4 or etch\$4)) and ((photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or var\$5 or chang\$4) same (efficienc\$4 or captur\$4 or absorb\$4 or absorp\$4) same electron)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
3	151	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) same (thin\$4 or etch\$4)) and ((photo\$4active\$4acid\$4gener at\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or var\$5 or chang\$4) same (expos\$4 or irradiat\$\$ or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
4	7	<p>((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) same (thin\$4 or etch\$4)) and ((photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or var\$5 or chang\$4) same (expos\$4 or irradiat\$\$ or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV)) and (secondary near9 electron)</p>	<p>US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB</p>

	Hits	Search Text	DBs
5	86	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) same (thin\$4 or etch\$4)) and ((photo\$4active\$4acid\$4gener at\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or var\$5 or chang\$4) same (expos\$4 or irradiat\$\$ or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV)) and ((high\$4 near6 (absor\$5 or sensitiv\$6)) same (resist or photoresist))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
6	1	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) same (thin\$4 or etch\$4)) and ((photo\$4active\$4acid\$4gener at\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or var\$5 or chang\$4 adjust\$4) same (expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV)) and (etch\$6resistant near5 (deposit\$4 or layer or coat\$4 or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	3	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) same (thin\$4 or etch\$4)) and ((photo\$4active\$4acid\$4gener at\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or var\$5 or chang\$4 adjust\$4) same (expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV)) and (etch\$6resist\$4 same (deposit\$4 or layer or coat\$4 or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
8	16	<p>((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) same (thin\$4 or etch\$4)) and ((photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or var\$5 or chang\$4 adjust\$4)) and ((expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV)) and ((resist or photoresist or photo\$3imagea\$4 or photocur\$4) same (fluoro\$3polymer\$4 or (metallocene near5 polymer\$5) or (alkoxide nera6 chelate\$5) or (carboxylate near6 chelate)))</p>	<p>US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB</p>

	Hits	Search Text	DBs
9	194	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4))) and ((photo\$4active\$4acid\$4gener at\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or var\$5 or chang\$4 adjust\$4)) and ((expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV)) and ((resist or photoresist or photo\$3imagea\$4 or photocur\$4) same (fluoro\$3 or fluorine or (metallocene near9 polymer\$5) or (alkoxide nera6 chelate\$5) or (carboxylate near6 chelate)) same (etch\$4 or thin\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
10	5	<p>((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4))) and ((photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or var\$5 or chang\$4 adjust\$4)) and ((expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV)) and ((resist or photoresist or photo\$3imagea\$4 or photocur\$4) same (fluoro\$3 or fluorine or (metallocene near9 polymer\$5) or (alkoxide nera6 chelate\$5) or (carboxylate near6 chelate)) same (etch\$4 or thin\$4)) and (second\$5 near9 electron)</p>	<p>US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB</p>

	Hits	Search Text	DBs
11	48	(resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) and (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) and ((photo\$4active\$4acid\$4gener at\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or var\$5 or chang\$4 adjust\$4)) and ((expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV) same (resist or photoresist or photo\$3imagea\$4 or photocur\$4) same (etch\$4 or thin\$4)) and (second\$5 near9 electron)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
12	11	(resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) and (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) and ((photo\$4active\$4acid\$4gener at\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or var\$5 or chang\$4 adjust\$4)) and ((expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV) same (resist or photoresist or photo\$3imagea\$4 or photocur\$4) same (etch\$4 or thin\$4)) and (secondary near9 electron)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
13	0	(resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) and (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) and ((photo\$4active\$4acid\$4gener at\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or varying or variable or alter\$3 or chang\$4 adjust\$4)) and ((expos\$4 or irradiat\$4 or illuminat\$4) same (ion or e\$3beam or (electron near4 beam) or X\$4ray or EUV) same (resist or photoresist or photo\$3imagea\$4 or photocur\$4) same (etch\$4 or thin\$4)) and (secondary near9 electron)	USOCR

	Hits	Search Text	DBs
14	5	(resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) and (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 generat\$4) or (acid near5 generat\$4)) and ((photo\$4active\$4acid\$4gener at\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (concentration or amount or increas\$4 or varying or variable or alter\$3 or chang\$4 adjust\$4)) and ((expos\$4 or irradiat\$4 or illuminat\$4) same (ion or e\$3beam or (electron near4 beam) or X\$4ray or EUV) same (resist or photoresist or photo\$3imagea\$4 or photocur\$4) same (etch\$4 or thin\$4)) and (secondary near3 electron)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
15	89	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (coat\$4 or spin\$4coat\$4 or deposit\$4) same (uniform\$3 or thin\$4 or etch\$4)) and ((resist or photoresist or etch\$4resist\$4) same (dual or second or top\$3resist or (upper near5 layer) or (top near4 layer)) same (expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV or ion\$4beam))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
16	23	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (coat\$4 or spin\$4coat\$4 or deposit\$4) same (uniform\$3 or thin\$4 or etch\$4)) and ((resist or photoresist or etch\$4resist\$4) same ((dual near4 layer) or (double near5 layer) or (second near9 layer) or top\$3resist or (upper near5 layer) or (top near4 layer)) same (expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV or ion\$4beam))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
17	6	<p>((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (coat\$4 or spin\$4coat\$4 or deposit\$4) same (uniform\$3 or thin\$4 or etch\$4)) and ((resist or photoresist or etch\$4resist\$4) same ((dual near4 layer) or (double near5 layer) or (second near9 layer) or top\$3resist or (upper near5 layer) or (top near4 layer)) same (expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV or ion\$4beam)) and ((photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 (liberat\$4 or generat\$4)) or PAG or photo\$8generat\$4) same (increas\$4 or var\$5 or chang\$4 adjust\$4 or alter\$4))</p>	<p>US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB</p>

	Hits	Search Text	DBs
18	37	<p>((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (coat\$4 or spin\$4coat\$4 or deposit\$4) same (uniform\$3 or thin\$4 or etch\$4)) and ((resist or photoresist or etch\$4resist\$4) same (dual or second or top\$3resist or (upper near5 layer) or (top near4 layer)) same (expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV or ion\$4beam)) and ((photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 (liberat\$4 or generat\$4)) or PAG or photo\$8generat\$4) near9 (increas\$4 or var\$5 or chang\$4 adjust\$4 or alter\$4))</p>	<p>US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB</p>

	Hits	Search Text	DBs
19	15	<p>((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (coat\$4 or spin\$4coat\$4 or deposit\$4) same (uniform\$3 or thin\$4 or etch\$4)) and ((resist or photoresist or etch\$4resist\$4) same (expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV or ion\$4beam)) and ((photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 (liberat\$4 or generat\$4)) or PAG or photo\$8generat\$4) near9 (increas\$4 or var\$5 or chang\$4 adjust\$4 or alter\$4) near9 (amount or concentration or volume))</p>	<p>US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB</p>

	Hits	Search Text	DBs
20	13	<p>((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (coat\$4 or spin\$4coat\$4 or deposit\$4) same (uniform\$3 or thin\$4 or etch\$4)) and ((resist or photoresist or etch\$4resist\$4) same (dual or second or top\$3resist or (upper near5 layer) or (top near4 layer)) same (expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV or ion\$4beam)) and (((photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 (liberat\$4 or generat\$4)) or PAG or photo\$8generat\$4) near9 (increas\$4 or var\$5 or chang\$4 adjust\$4 or alter\$4 or control\$4)) same (moiet\$4 or group or (function\$3 near4 group)))</p>	<p>US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB</p>

	Hits	Search Text	DBs
21	60	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4genera t\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (coat\$4 or spin\$4coat\$4 or deposit\$4) same (uniform\$3 or thin\$4 or etch\$4)) and (((photo\$4active\$4acid\$4gene rat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 (liberat\$4 or generat\$4)) or PAG or photo\$8generat\$4) near9 (increas\$4 or var\$5 or chang\$4 adjust\$4 or alter\$4 or control\$4)) same (moiet\$4 or group or (function\$3 near4 group)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
22	0	<p>((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (coat\$4 or spin\$4coat\$4 or deposit\$4) same (uniform\$3 or thin\$4 or etch\$4)) and (((photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 (liberat\$4 or generat\$4)) or PAG or photo\$8generat\$4) near9 (increas\$4 or varying or variable or varied or chang\$4 adjust\$4 or alter\$4 or control\$4)) same (moiet\$4 or group or (function\$3 near4 group)))</p>	USOCR

	Hits	Search Text	DBs
23	0	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (coat\$4 or spin\$4coat\$4 or deposit\$4) same (uniform\$3 or thin\$4 or etch\$4)) and ((resist or photoresist or etch\$4resist\$4) same (dual or second or top\$3resist or (upper near5 layer) or (top near4 layer)) same (expos\$4 or irradiat\$4 or illuminat\$4) same (ion\$5 or e\$3beam or (electron near4 beam) or X\$4ray or EUV or ion\$4beam)) and (secondary near3 electron)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
24	4	((resist or photoresist or photosensitive or radiation\$4sensitive or photocur\$4) same (photo\$4active\$4acid\$4generat\$4 or (photoacid near5 (liberat\$4 or generat\$4)) or (acid near5 generat\$4) or PAG or photo\$8generat\$4) same (coat\$4 or spin\$4coat\$4 or deposit\$4) same (uniform\$3 or thin\$4 or etch\$4)) and (secondary near3 electron)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB